

# **PSMN016-100PS**

## N-channel 100V 16 m $\Omega$ standard level MOSFET in TO-220

Rev. 3 — 27 September 2011

**Product data sheet** 

## 1. Product profile

## 1.1 General description

Standard level N-channel MOSFET in a TO220 packages qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I <sub>D</sub>	drain current	$T_j = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	-	-	57	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	148	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
Doon	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A}; V_{DS} = 50 \text{ V};$	-	15	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15	-	49	-	nC
Avalanch	ne ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 ^{\circ}\text{C};$ $I_D = 60 \text{ A}; V_{sup} \le 100 \text{ V};$ unclamped; $R_{GS} = 50 \Omega$	-	-	101	mJ



## 2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
	S	source		
mb	D	mounting base; connected to drain		mbb076 Š
			SOT78 (TO-220AB)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN016-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{see } \frac{\text{Figure 1}}{\text{Model}}$	-	40	Α
		$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	57	Α
$I_{DM}$	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	230	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	148	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	57	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	230	Α
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 60 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	101	mJ

PSMN016-100PS

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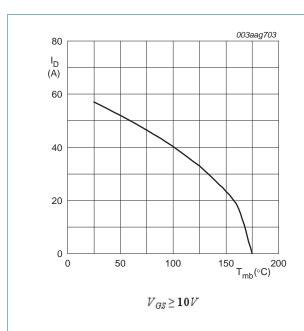


Fig 1. Continuous drain current as a function of mounting base temperature

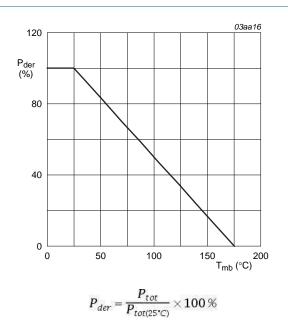
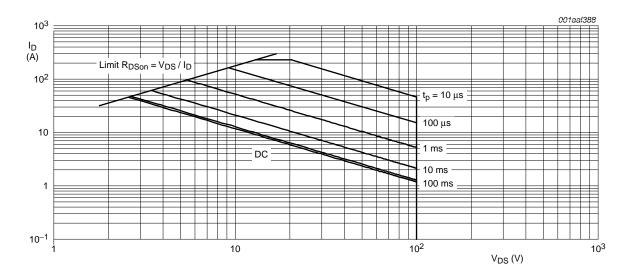


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.56	1.01	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		<u>[1]</u> -	50	-	K/W

[1] minimum footprint; mounted on a printed-circuit board to ambient

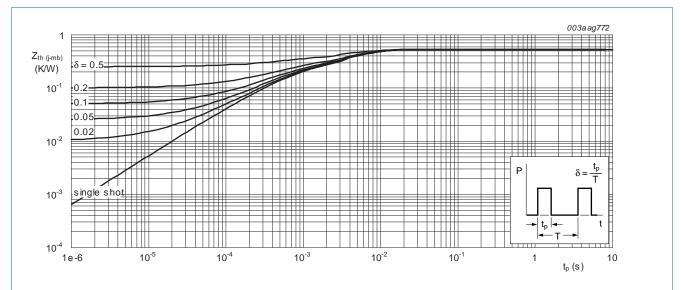


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 6. Characteristics

Table 6. Characteristics

Ch	haracteristics					
	Parameter	Conditions	Min	Тур	Max	Unit
haract	cteristics					
6	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10	-	-	4.8	V
	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	36.4	44.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
c chai	aracteristics					
	total gate charge	$I_D = 0 A$ ; $V_{DS} = 0 V$ ; $V_{GS} = 10 V$ ; see <u>Figure 14</u>	-	40	-	nC
		$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	49	-	nC
	gate-source charge	see Figure 14; see Figure 15	-	12	-	nC
	pre-threshold gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	7.75	-	nC
,	post-threshold gate-source charge		-	4.25	-	nC
	gate-drain charge	$I_D = 30 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	15	-	nC
	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.5	-	V
	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2404	-	pF
	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	189	-	pF
	reverse transfer capacitance		-	113	-	pF
	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.7 \Omega; V_{GS} = 10 \text{ V};$	-	17	-	ns
	rise time	$H_{G(ext)} = 4.7 \Omega; T_j = 25 \degree C$	-	23	-	ns
	turn-off delay time		-	36	-	ns
	fall time		-	18	-	ns
	rise time turn-off delay time	$R_{G(ext)} = 4.7 \Omega$ ; $T_j = 25 °C$	-	23 36	-	

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	54	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	126	-	nC

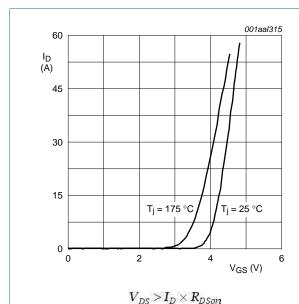


Fig 5. Transfer Characteristic: drain current as a function of gate-source voltage; typical values

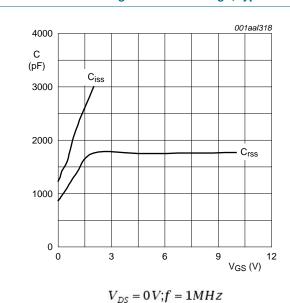
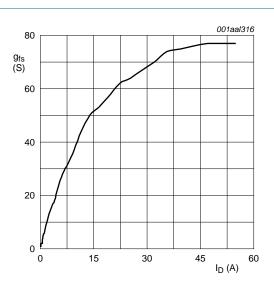
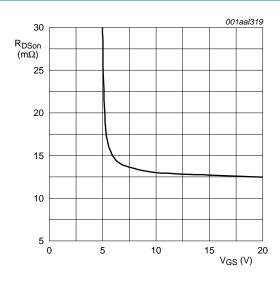


Fig 7. Input and revers transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$ 

Fig 6. forward transconductance as a function of drain current; typical values



 $T_j=25\,^{\circ}C; I_D=5A$ 

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

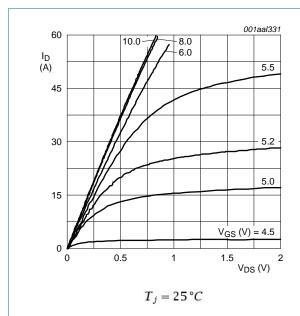


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

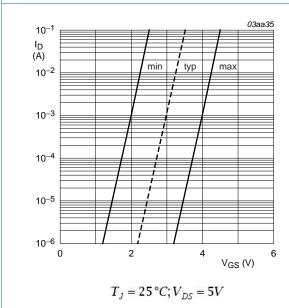


Fig 11. Sub-threshold drain current as a function of gate-source voltage

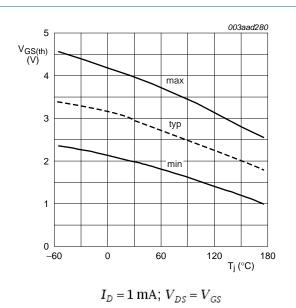


Fig 10. Gate-source threshold voltage as a function of junction temperature

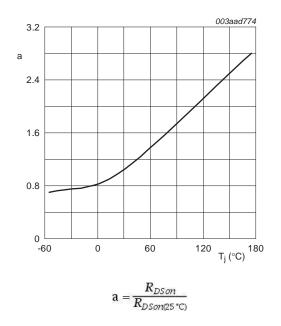
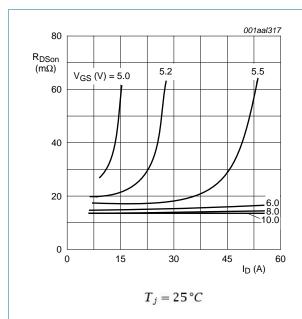


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V<sub>GS</sub>(pl)

V<sub>GS</sub>(th)

V<sub>GS</sub>(th)

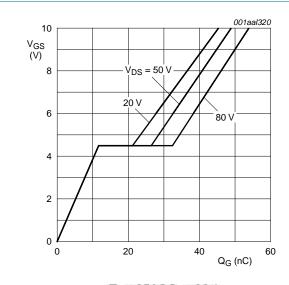
Q<sub>GS1</sub> Q<sub>GS2</sub>

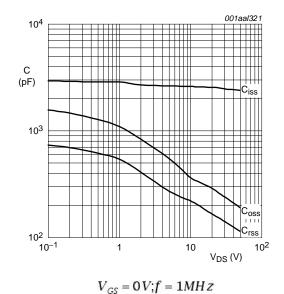
Q<sub>GS</sub> Q<sub>G</sub>(tot)

003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values







 $T_j = 25\,^{\circ}C; I_D = 30A$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 15. Gate-source voltage as a function of gate charge; typical values

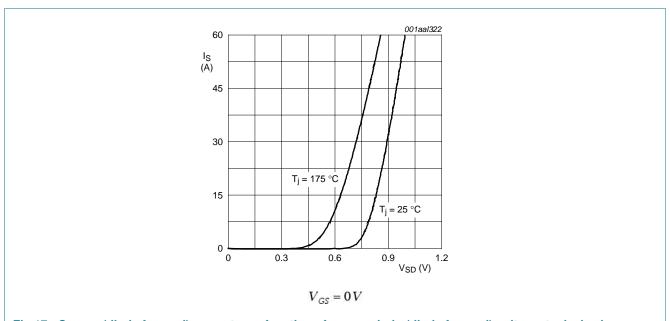
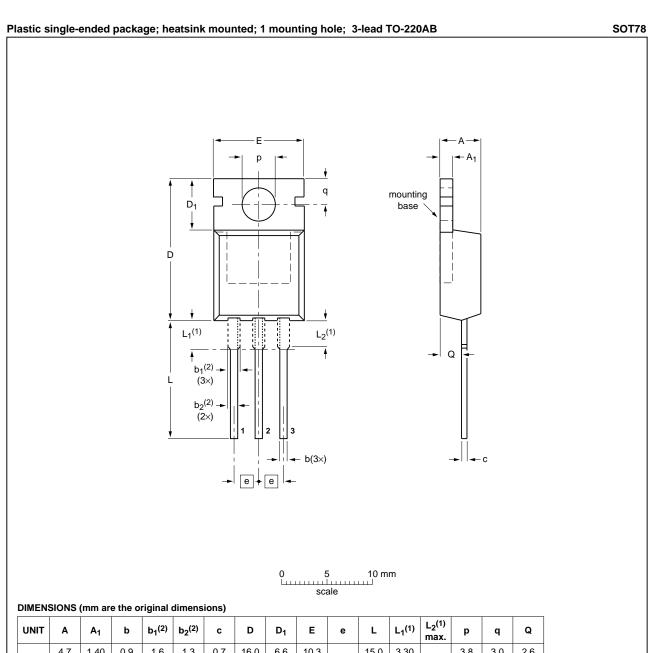


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## Package outline



UNI	ГА	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN016-100PS

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## 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100PS v.3	20110927	Product data sheet	-	PSMN016-100PS v.2
Modifications:	<ul> <li>Various changes to</li> </ul>			
PSMN016-100PS v.2	20110721	Product data sheet	-	PSMN016-100PS v.1

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PSMN016-100PS**

#### N-channel 100V 16 mΩ standard level MOSFET in TO-220

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## 11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	4
6	Characteristics	5
7	Package outline	0
8	Revision history1	1
9	Legal information1	2
9.1	Data sheet status	2
9.2	Definitions1	2
9.3	Disclaimers	2
9.4	Trademarks1	3
10	Contact information1	3